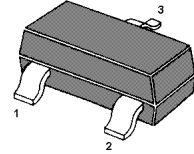
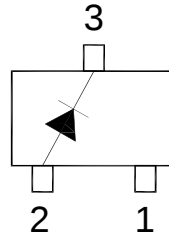


SDB531S

Silicon Epitaxial Planar Schottky Barrier Diode

High frequency rectification



Marking Code: **FJ**
SOT-23 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	30	V
Reverse Voltage	V_R	30	V
Average Forward Current	$I_{F(AV)}$	1	A
Non-repetitive Peak Surge Current	I_{FSM}	10	A
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 125	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Typ.	Max.	Unit
Forward Voltage at $I_F = 0.5\text{ A}$ at $I_F = 1\text{ A}$	V_F	- -	0.4 0.47	V
Reverse Current at $V_R = 15\text{ V}$ at $V_R = 30\text{ V}$	I_R	- -	500 1000	μA
Junction Capacitance at $V_R = 10\text{ V}$, $f = 1\text{ MHz}$	C_j	35	-	pF
Reverse Recovery Time at $I_F = I_R = 100\text{ mA}$	t_{rr}	-	15	ns

TOP DYNAMIC



Dated: 21/06/2016 Rev: 01

